

6-16GHz Low Noise Amplifier

GaAs Monolithic Microwave IC in SMD package

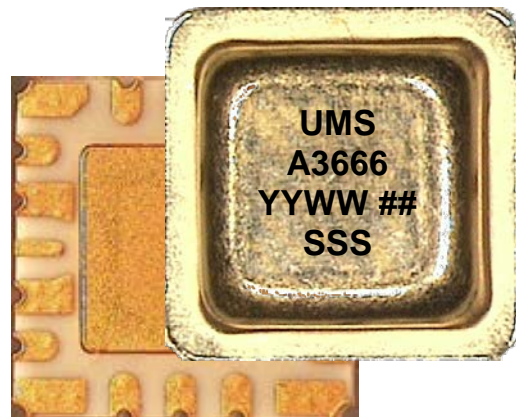
Description

The CHA3666-FAB is a two-stage self-biased wide band monolithic low noise amplifier.

The circuit is manufactured with a standard pHEMT process: 0.25 μ m gate length, via holes through the substrate, air bridges and electron beam gate lithography.

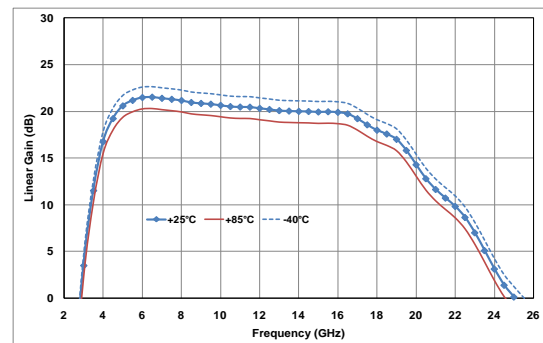
It is proposed in leadless surface mount hermetic metal ceramic 6x6mm² package. The overall power supply is of 4V/80mA.

The circuit is dedicated to space applications and also well suited for a wide range of microwave and millimetre wave applications and systems.



Main Features

- Broadband performance 6-16GHz
- 1.8dB typical Noise Figure
- 24dBm 3rd order intercept point
- 16dBm power at 1dB compression
- 21dB gain
- Low DC power consumption
- 6x6mm² metal ceramic hermetic package



Main Electrical Characteristics

Tamb.= +25°C

Symbol	Parameter	Min	Typ	Max	Unit
Fop	Operating frequency range	6		16	GHz
NF	Noise figure		1.8	2.5	dB
G	Small signal Gain	18.5	21		dB
IP3	3rd order intercept point		24		dBm

ESD Protections: Electrostatic discharge sensitive device observe handling precautions!

Electrical Characteristics⁽¹⁾

Tamb.= +25°C, Vd1 = Vd2 = +4.0V, P1 and N2 grounded, P2: NC.

Symbol	Parameter	Min	Typ	Max	Unit
Fop	Operating frequency range	6		16	GHz
G	Gain	18.5	21		dB
ΔG	Gain flatness		±1		dB
NF	Noise figure		1.8	2.5	dB
IS11I	Input return loss		7	6.5	dB
IS22I	Output return loss		10	8.5	dB
IP3	3rd order intercept point		26		dBm
P1dB	Output power at 1dB gain comp.	15	17		dBm
Vd1, Vd2	Drain bias voltage		4		V
Id	Drain bias current	60	80	100	mA

⁽¹⁾ These values are representative of on board measurements as defined on the drawing 99622 (see below).

Absolute Maximum Ratings ⁽¹⁾

Tamb.= +25°C

Symbol	Parameter	Values	Unit
Vd	Drain bias voltage (Vd1 & Vd2)	4.5	V
Pin	Maximum peak input power overdrive ⁽⁴⁾	10	dBm
Top	Operating temperature range ⁽²⁾	-40 to +85	°C
Tj	Junction temperature ⁽³⁾	175	°C
Tstg	Storage temperature range	-55 to +150	°C

⁽¹⁾ Operation of this device above any one of these parameters may cause permanent damage.

⁽²⁾ Top = Package Ground Paddle back side temperature

⁽³⁾ Thermal Resistance channel to ground paddle = 214°C/W for T_{ground paddle} = +85°C

⁽⁴⁾ Duration < 1s.

Typical Package Sij parameters

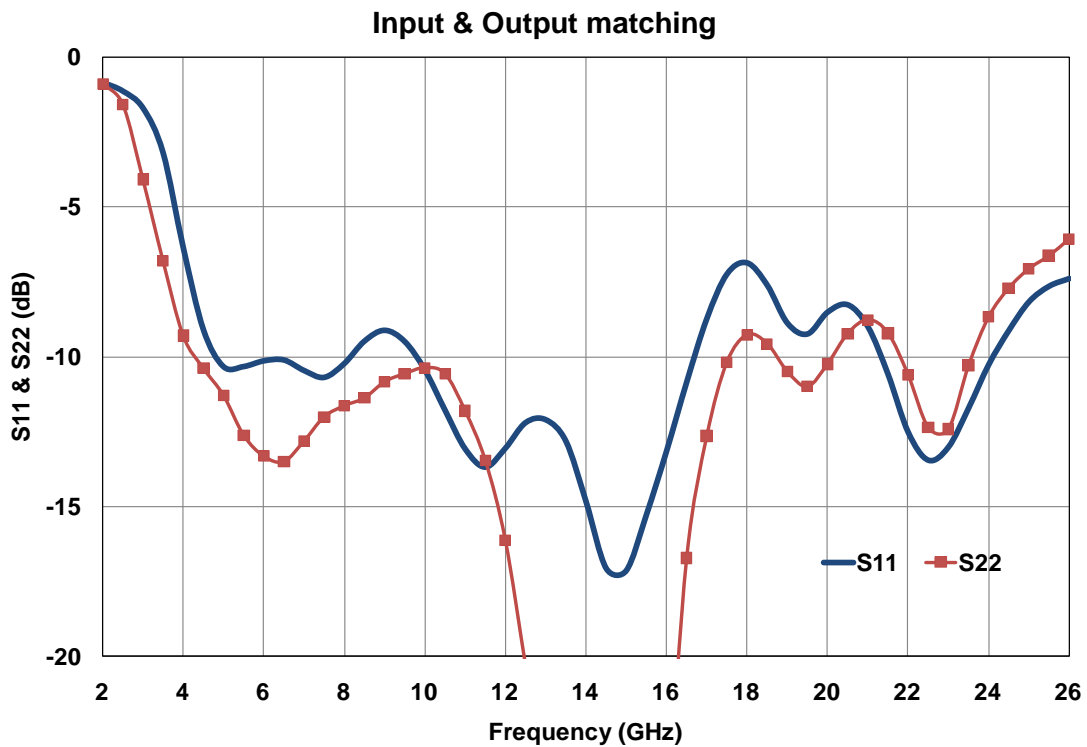
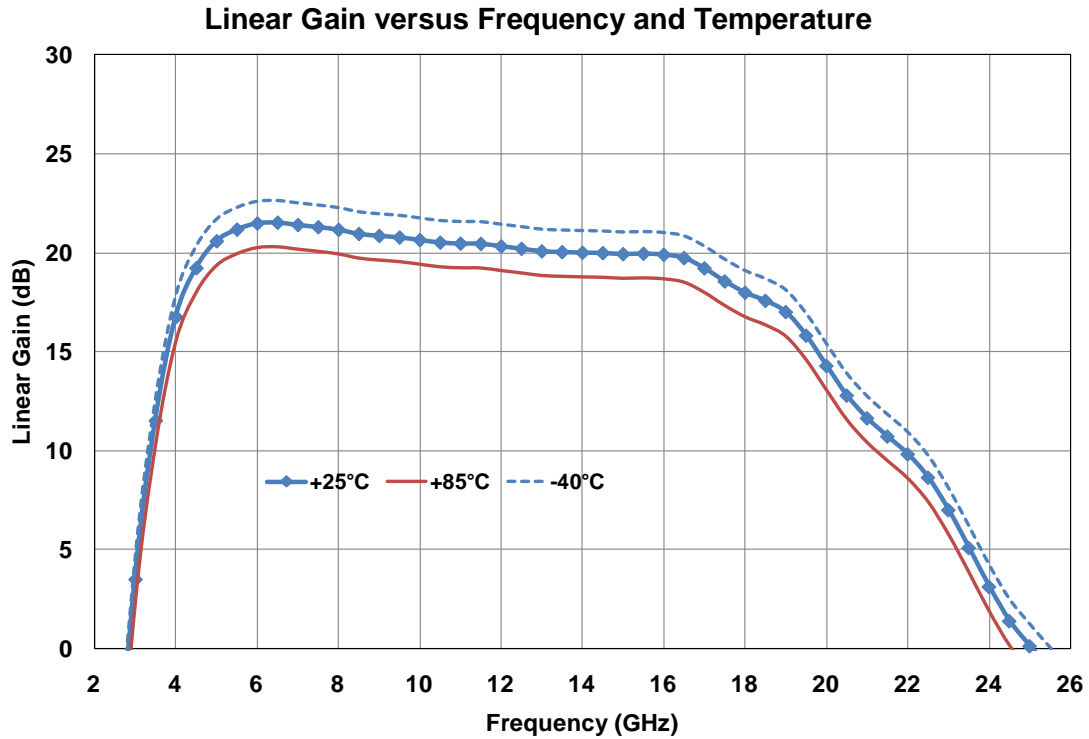
For low current configuration in 99622 board - in connector plane

Temp = +25°C, Vd1 = Vd2 = +4.0V, P1 and N2 grounded, P2: NC, typical Id=80mA

FREQ (GHz)	dBS11	PhS11 (°)	dBS12	PhS12 (°)	dBS21	PhS21 (°)	dBS22	PhS22 (°)
1.0	-0.28	-128.50	-77.75	166.70	-51.19	155.80	-0.37	-135.00
2.0	-0.86	106.10	-65.63	41.41	-31.56	145.10	-0.89	99.75
3.0	-1.71	-35.04	-59.27	-156.30	3.47	-4.84	-4.09	-47.00
3.5	-3.19	-124.40	-66.37	123.50	11.50	-114.90	-6.81	-113.00
4.0	-6.34	127.50	-56.70	-148.20	16.74	137.80	-9.30	-169.60
4.5	-9.09	12.02	-49.61	127.20	19.21	37.78	-10.39	132.20
5.0	-10.33	-90.74	-45.83	42.90	20.57	-54.26	-11.29	76.93
5.5	-10.33	-172.60	-43.97	-31.81	21.16	-140.50	-12.62	18.97
6.0	-10.14	123.50	-42.56	-104.60	21.47	138.10	-13.32	-38.24
6.5	-10.11	66.93	-41.42	-176.30	21.51	60.52	-13.50	-103.90
7.0	-10.46	9.32	-40.56	113.20	21.39	-14.15	-12.82	-172.70
7.5	-10.69	-50.07	-40.07	44.29	21.28	-86.67	-12.01	117.50
8.0	-10.23	-109.20	-39.91	-21.61	21.15	-157.40	-11.64	48.26
8.5	-9.48	-164.80	-39.61	-86.89	20.94	133.30	-11.38	-19.82
9.0	-9.12	141.10	-39.51	-149.00	20.84	65.44	-10.84	-88.89
9.5	-9.49	85.88	-39.08	154.40	20.76	-2.64	-10.57	-155.70
10.0	-10.44	26.06	-38.25	91.93	20.63	-69.59	-10.37	144.50
10.5	-11.78	-37.75	-37.66	30.13	20.50	-136.30	-10.57	87.39
11.0	-13.07	-109.10	-37.26	-33.42	20.45	158.10	-11.81	34.84
11.5	-13.68	174.50	-37.27	-95.94	20.44	91.47	-13.46	-12.50
12.0	-13.05	103.60	-37.08	-159.30	20.31	25.43	-16.13	-62.27
12.5	-12.20	45.30	-37.12	136.70	20.19	-40.34	-20.30	-120.50
13.0	-12.10	-2.70	-37.45	73.45	20.06	-105.60	-24.41	148.00
13.5	-12.81	-48.77	-37.78	9.75	20.02	-170.90	-22.31	55.05
14.0	-14.82	-99.42	-37.93	-55.40	19.99	123.50	-21.13	-1.25
14.5	-17.05	-164.90	-38.14	-121.50	19.97	57.62	-21.82	-42.80
15.0	-17.13	119.30	-38.40	171.50	19.92	-8.40	-24.38	-83.61
15.5	-15.27	55.44	-39.04	103.10	19.94	-75.39	-33.30	-120.40
16.0	-13.15	-3.86	-39.57	36.40	19.89	-142.80	-25.55	1.44
16.5	-10.85	-65.66	-40.44	-29.32	19.72	148.50	-16.72	-51.31
17.0	-8.74	-128.80	-41.38	-100.40	19.20	79.58	-12.65	-99.21
17.5	-7.25	172.40	-43.33	-170.80	18.54	11.96	-10.18	-150.90
18.0	-6.87	116.20	-46.35	120.50	17.97	-54.40	-9.27	154.30
18.5	-7.62	55.87	-52.17	41.48	17.56	-121.90	-9.57	94.52
19.0	-8.88	-17.09	-61.92	-122.90	16.99	168.20	-10.50	24.24
19.5	-9.24	-97.74	-50.18	106.00	15.80	97.90	-11.00	-54.27
20.0	-8.52	-166.40	-45.56	38.93	14.27	30.72	-10.24	-128.70
21.0	-9.00	76.44	-40.89	-93.87	11.62	-96.01	-8.77	105.90
22.0	-12.52	-62.64	-37.85	135.90	9.80	135.20	-10.62	-20.22
23.0	-13.01	129.00	-37.52	-12.50	6.98	2.37	-12.41	169.80
24.0	-10.26	-12.31	-40.15	-127.90	3.10	-121.80	-8.67	34.13
25.0	-8.17	-120.00	-41.30	123.20	0.10	123.60	-7.07	-84.59
26.0	-7.40	128.10	-39.97	6.46	-2.23	7.45	-6.07	158.90
27.0	-6.57	14.08	-40.77	-111.10	-4.48	-105.10	-5.53	48.83
28.0	-6.56	-86.86	-40.69	131.30	-5.23	146.00	-5.49	-58.77
29.0	-8.17	151.20	-39.63	9.70	-4.25	27.54	-5.63	-166.40
30.0	-6.89	22.64	-38.52	-116.10	-3.67	-104.50	-5.39	85.11

Typical boards Measurements

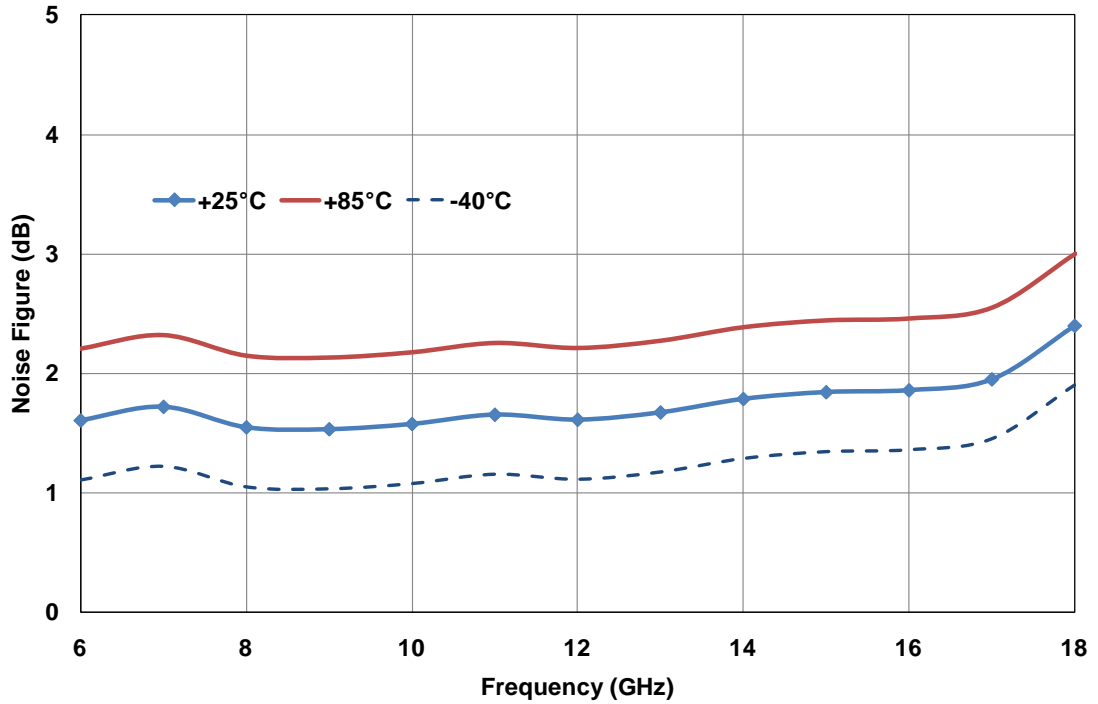
Temp = +25°C, Vd1 = Vd2 = +4.0V, P1 and N2 grounded, P2: NC, typical Id=80mA
Measurements in the connector planes, using the proposed land pattern & board 99622.



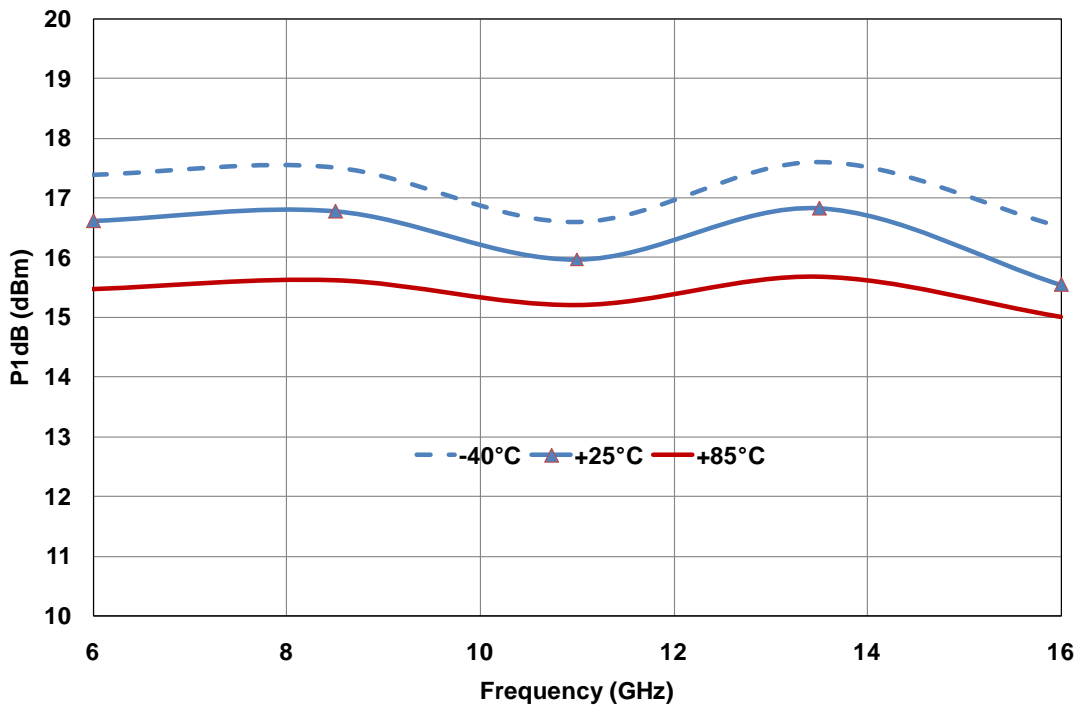
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Temp = +25°C, Vd1 = Vd2 = +4.0V, P1 and N2 grounded, P2: NC, typical Id=80mA
 Measurements in the connector planes, using the proposed land pattern & board 99622.

Noise Figure versus Frequency and Temperature



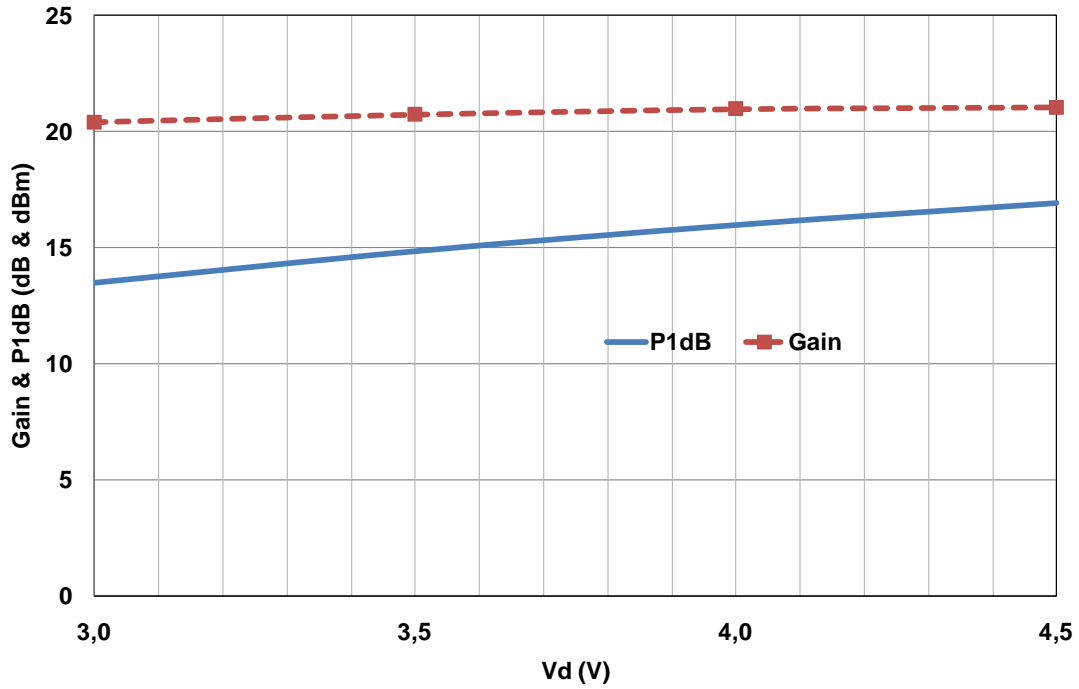
Output power at 1dB compression versus frequency



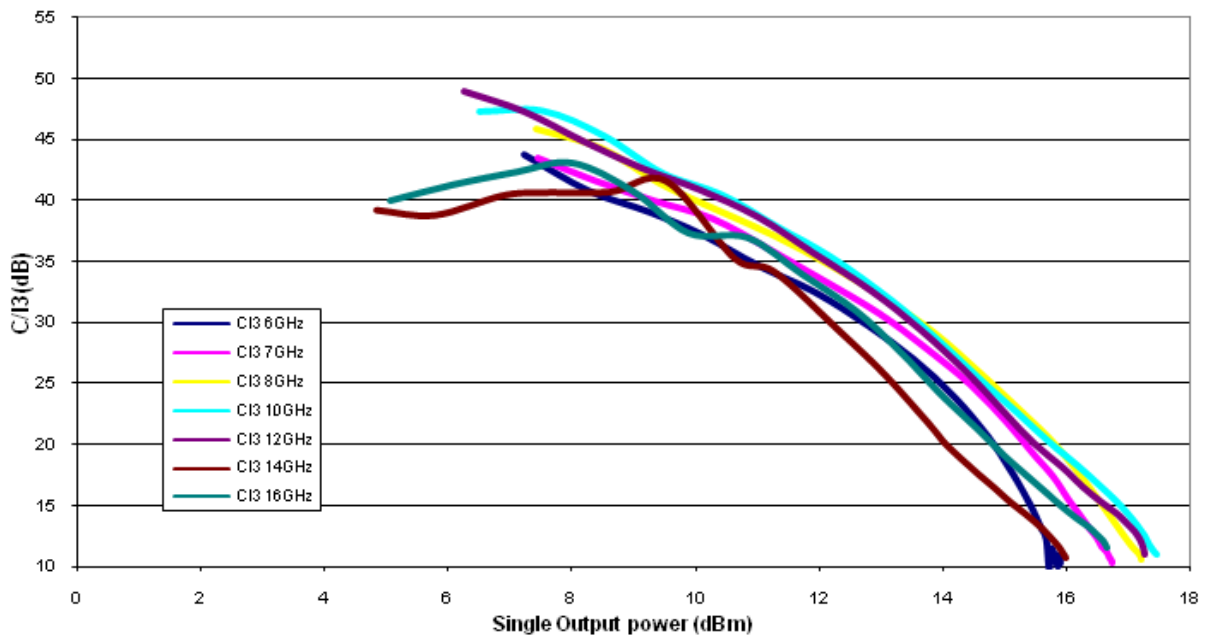
Typical boards Measurements

Temp = +25°C, Vd1 = Vd2 = +4.0V, P1 and N2 grounded, P2: NC, typical Id=80mA
 Measurements in the connector planes, using the proposed land pattern & board 99622.

Output power at 1dB compression and Linear Gain versus Drain Voltage (F=11GHz)



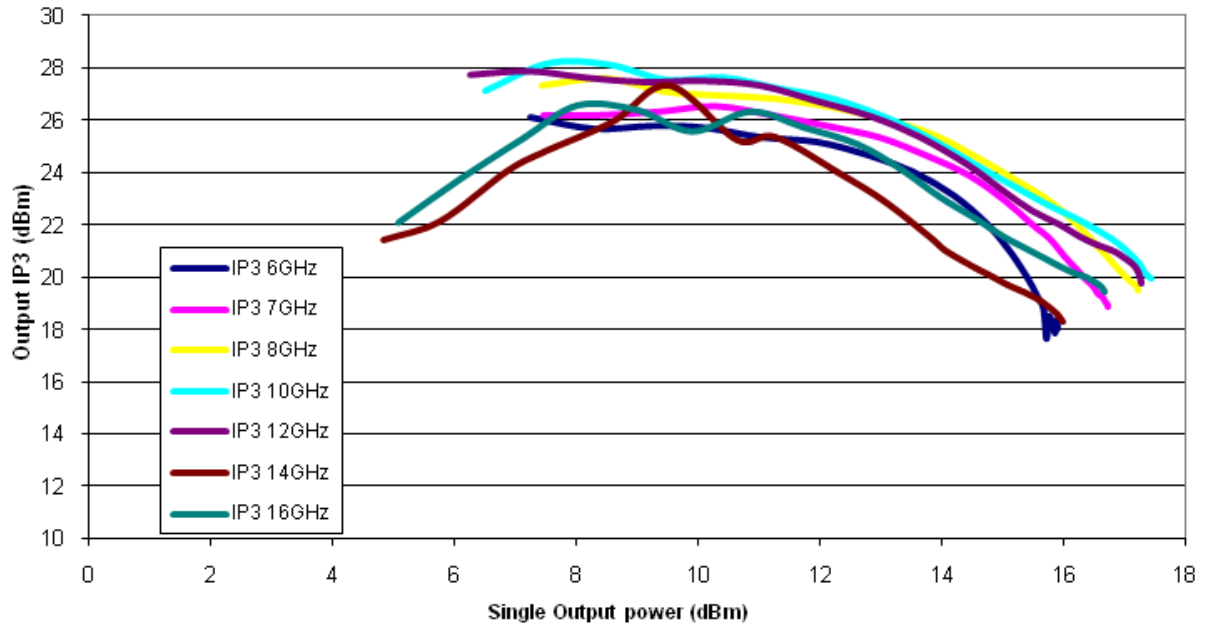
C/I3 versus output power



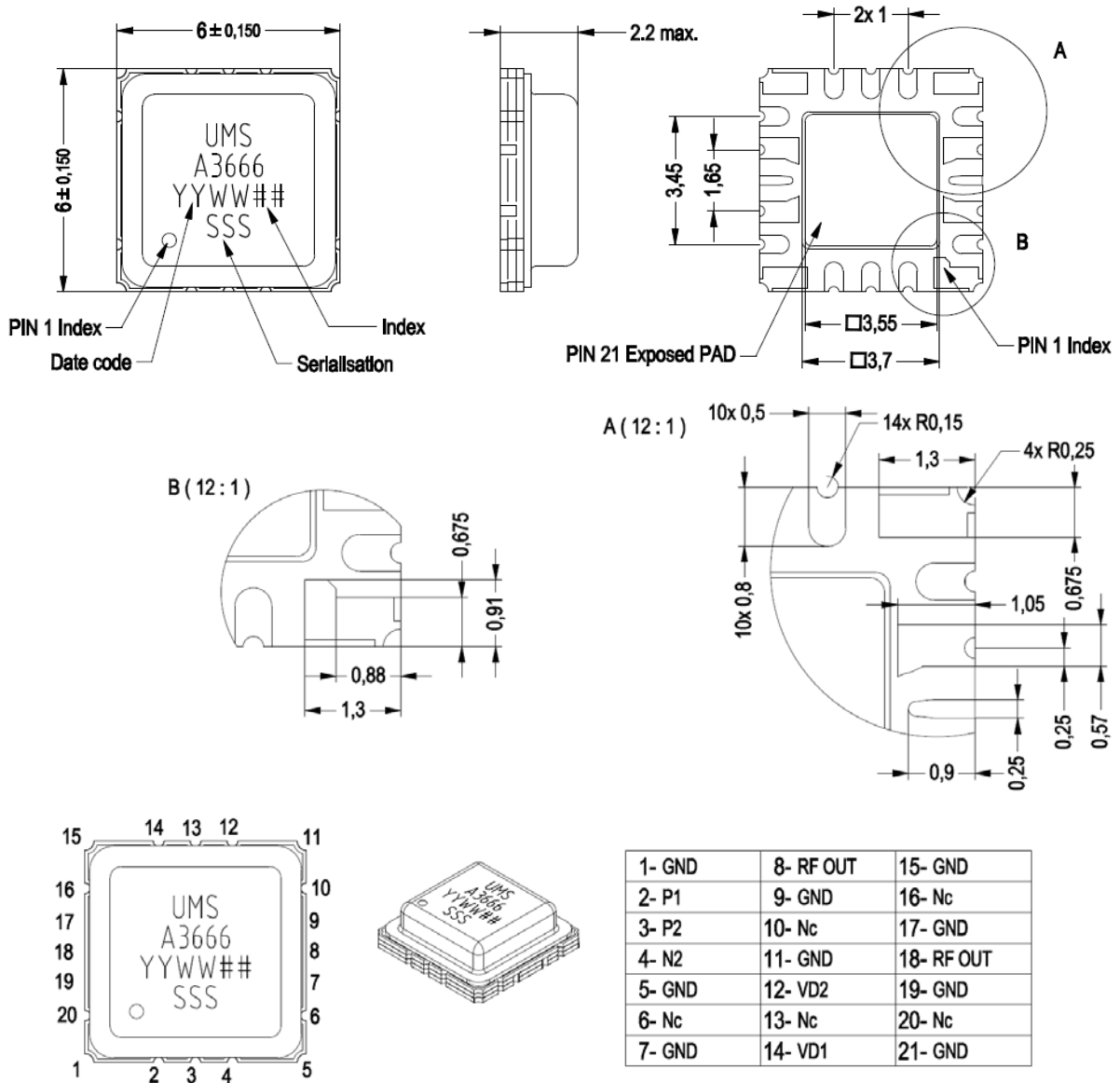
Typical boards Measurements

Temp = +25°C, Vd1 = Vd2 = +4.0V, P1 and N2 grounded, P2: NC, typical Id=80mA
 Measurements in the connector planes, using the proposed land pattern & board 99622.

Output IP3 versus output power



Package outline ⁽¹⁾

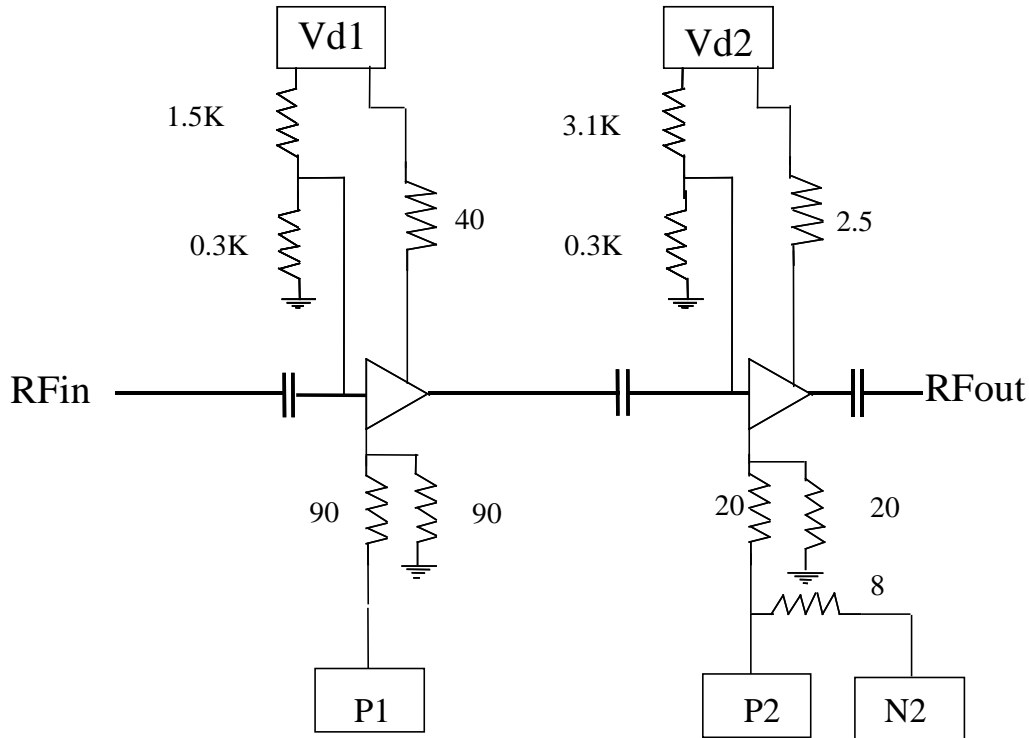


All dimensions are in mm

⁽¹⁾ It is strongly recommended to ground all pins marked "Gnd" through the PCB board. Ensure that the PCB board is designed to provide the best possible ground to the package.

DC Schematic

This chip is self-biased, and flexibility is provided by the access to number of leads. The internal DC electrical schematic is given in order to use these leads in a safe way.



Two standard biasing:

Low Noise and low consumption:

Vd1=Vd2 = 4V and P1, N2 grounded.
P2 pads non connected (NC).
Idd = 80mA & Pout-1dB = 16dBm Typical.

Low Noise and higher output power:

Vd1=Vd2 = 4V and P1, P2 grounded.
N2 pads non connected (NC).
Idd = 85mA & Pout-1dB = 16.5dBm Typical.

Note



SMD mounting procedure

For the mounting process standard techniques involving solder paste and a suitable reflow process can be used. For further details, see application note AN0017 available at <http://www.ums-gaas.com>.

Recommended environmental management

UMS products are compliant with the regulation in particular with the directives RoHS N°2011/65 and REACH N°1907/2006. More environmental data are available in the application note AN0019 also available at <http://www.ums-gaas.com>.

Recommended ESD management

Refer to the application note AN0020 available at <http://www.ums-gaas.com> for ESD sensitivity and handling recommendations for the UMS package products.

FAB Type Surface Mount Hermetic Package

Refer to the application note AN0024 available at <http://www.ums-gaas.com> for assembly recommendations for the UMS FAB package products.

Ordering Information

Leadless hermetic package: CHA3666-FAB/XY
Waffle pack: XY=24

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